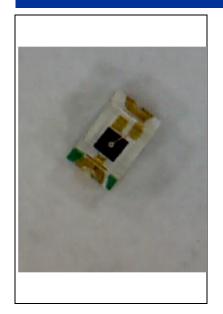
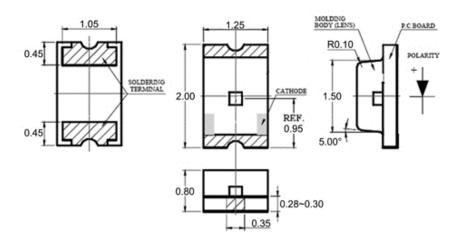


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# **Precision – Control – Results**



## 0805 PACKAGE DIMENSIONS, MM



#### **DESCRIPTION**

The **SD 019-101-411** is a silicon PIN 0.18mm² active area, UV enhanced photodiode, assembled in a 0805 SMT package.

#### **FEATURES**

- Small Footprint
- Low Capacitance
- High Speed

### **RELIABILITY**

This API high-reliability detector is in principle able to meet military test requirements (Mil-STD-750, Mil-STD-883) after proper screening and group test.

Contact API for recommendations on specific test conditions and procedures.

# **APPLICATIONS**

- Industrial Sensors
- Light Management
- Handheld Devices

#### **ABSOLUTE MAXIMUM RATINGS**

 $T_a = 25$ °C UNLESS OTHERWISE NOTED

| PARAMETER              | MIN | MAX  | UNITS |
|------------------------|-----|------|-------|
| Reverse Voltage        | -   | 50   | V     |
| Operating Temperature  | -40 | +105 | °C    |
| Storage Temperature    | -50 | +125 | °C    |
| Soldering Temperature* | -   | +260 | °C    |

# Surface-Mount Photodiode Assembly

SD019-101-411

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|--|-------------------------------------|-----|-----|-------------------------------|-------|--|
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| <b>OPTO-ELECTRICAL PARAMETERS</b> T <sub>a</sub> = 23°C unless noted otherwise |                                     |     |     |                               |       |  |
| PARAMETER  | TEST CONDITIONS                     | MIN | TYP | MAX                           | UNITS |  |
| Forward Voltage  | I <sub>f</sub> =10 mA               | 0.5 | 0.8 | 1.3                           | V     |  |
| Light Current (2856K)  | $V_R = 5V$ ; H = 1000 lux           | -   | 3.2 | -                             | μΑ    |  |
| Breakdown Voltage  | $I_R = 100 \mu A$                   | 50  | -   | -                             | V     |  |
| Shunt Resistance   | $V_{bias} = 10 \text{ mV}$          | -   | 2.0 | -                             | GΩ    |  |
| Dark Current   | V <sub>R</sub> = 10 V               | -   | -   | 0.5                           | nA    |  |
| Junction Capacitance   | $V_R = 5V$ ; $f = 1000 \text{ kHz}$ | -   | 6.0 | -                             | pF    |  |
| Rise Time  | $V_R = 3V; R_i = 1000\Omega$        | -   | 1.0 | -                             | μS    |  |

# **TYPICAL PERFORMANCE**

## **SPECTRAL RESPONSE**

